MAXIM

Complete 10μs CMOS 12-Bit ADC

General Description

The MAX172 is a complete 12-Bit analog-to-digital converter (ADC) that combines high speed, low power consumption, and an on-chip voltage reference. The conversion time is 10μs. The buried zener reference provides low drift and low noise performance.

External component requirements are limited to only decoupling capacitors for the power supply and reference voltages. On-chip clock circuitry is also included which can either be driven from an external source, or in stand-alone applications, can be used with a crystal.

The MAX172 uses a standard microprocessor interface architecture. Three-state data outputs are controlled by Read (RD) and Chip Select (CS) inputs. Data access and bus release times of 90 and 75ns respectively ensure compatibility with most popular microprocessors without resorting to wait states.

Applications

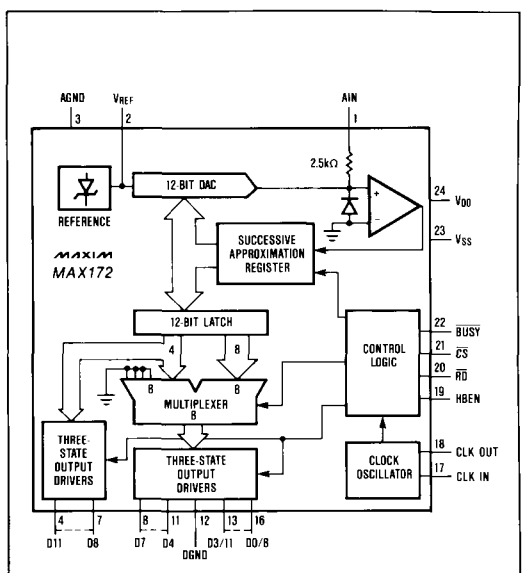
Digital Signal Processing (DSP)

High Accuracy Process Control

High Speed Data Acquisition

Electro-Mechanical Systems

Functional Diagram



Features

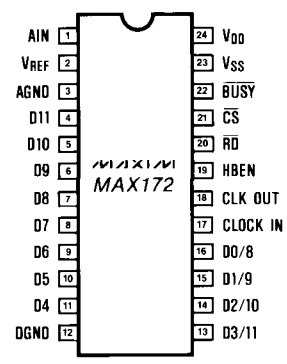
- **12-Bit Resolution and Linearity**
- **10μs Conversion Time**
- **No Missing Codes**
- **On-Chip Voltage Reference**
- **90ns Access Time**
- **215mW Max Power Consumption**
- **24-Lead Narrow DIP Package**
- **Pin-for-Pin AD7572 Replacement**

Ordering Information

PART	TEMP. RANGE	PACKAGE*	ERROR
MAX172ACNG	0°C to +70°C	Plastic DIP	±½ LSB
MAX172BCNG	0°C to +70°C	Plastic DIP	±1 LSB
MAX172ACWG	0°C to +70°C	Wide S.O.	±½ LSB
MAX172BCWG	0°C to +70°C	Wide S.O.	±1 LSB
MAX172CC/D	0°C to +70°C	Dice**	+1 LSB
MAX172AING	-25°C to +85°C	Plastic DIP	+½ LSB
MAX172BING	-25°C to +85°C	Plastic DIP	+1 LSB
MAX172AMRG	-55°C to +125°C	CERDIP	+½ LSB
MAX172BMRG	-55°C to +125°C	CERDIP	+1 LSB

* *All devices — 24 lead packages*
** *Consult factory for dice specifications*

Pin Configuration



ABSOLUTE MAXIMUM RATINGS

V_{DD} to DGND ..... -0.3V to +7V
V_{SS} to DGND ..... +0.3V to -17V
AGND to DGND ..... -0.3V, V_{DD} + 0.3V
AIN to AGND ..... -15V to +15V
Digital Input Voltage to DGND ..... -0.3V, V_{DD} + 0.3V
(Pins 17, 19-21)
Digital Output Voltage to DGND ..... -0.3V, V_{DD} + 0.3V
(pins 4-11, 13-16, 18, 22)

Operating Temperature Ranges
MAX172XC ..... 0°C to +70°C
MAX172XI ..... -25°C to +85°C
MAX172XM ..... -55°C to +125°C
Storage Temperature Range ..... -65°C to +160°C
Power Dissipation (any Package) to +75°C 1000mW
Derates Above +75°C by ..... 10mW/°C
Lead Temperature (Soldering 10 seconds) ..... +300°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(V_{DD} = +5V ± 5%, V_{SS} = -12V or -15V ± 5%; Slow Memory Mode; T_A = T_{MIN} to T_{MAX} unless otherwise noted, f_{CLK} = 1.25MHz.)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
ACCURACY							
Resolution				12			Bits
Integral NonLinearity	INL	MAX172A	T_A = 25°C			±1/2	LSB
		MAX172AC/AI MAX172AM MAX172B				±1/2 ±3/4 ±1	
Differential NonLinearity	DNL	Guaranteed Monotonic Over Temp.				±1	LSB
Offset Error (Note 1)		MAX172B	T_A = 25°C T_A = T_{MIN} to T_{MAX}			±4 ±6	LSB
		MAX172A	T_A = 25°C T_A = T_{MIN} to T_{MAX}			±3 ±4	
Full Scale Error (Note 2)		MAX172B	T_A = 25°C			±15	LSB
		MAX172A	T_A = 25°C			±10	
Full Scale Tempco (Notes 3, 4)						±45	ppm/°C
ANALOG INPUT							
Input Voltage Range				0		5	V
Input Current		AIN = 0V to +5V				3.5	mA
INTERNAL REFERENCE							
V_{REF} Output Voltage		T_A = 25°C		-5.2	-5.25	-5.3	V
V_{REF} Output Tempco (Note 5)					40		ppm/°C
Output Current Sink Capability		(Note 6)				500	μA
LOGIC INPUTS							
Input Low Voltage	V_{IL}	$\overline{CS}$, $\overline{RD}$, HBEN, CLKIN				0.8	V
Input High Voltage	V_{IH}	$\overline{CS}$, $\overline{RD}$, HBEN, CLKIN		2.4			V
Input Capacitance (Note 7)	C_{IN}	$\overline{CS}$, $\overline{RD}$, HBEN, CLKIN				10	pF
Input Current	I_{IN}	$\overline{CS}$, $\overline{RD}$, HBEN CLKIN	VIN = 0 to V_{DD}			±10 ±20	μA
LOGIC OUTPUTS							
Output Low Voltage	V_{OL}	D11-D0/8, $\overline{BUSY}$, CLKOUT I_{SINK} = 1.6mA				0.4	V
Output High Voltage	V_{OH}	D11-D0/8, $\overline{BUSY}$, CLKOUT I_{SOURCE} = 200μA		4			V
Floating State Leakage Current	I_{LKG}	D11-D0/8, V_{OUT} = 0V to V_{DD}				±10	μA
Floating State Output Capacitance (Note 7)	C_{OUT}					15	pF

ELECTRICAL CHARACTERISTICS (Continued)

(V_{DD} = +5V ± 5%, V_{SS} = -12V or -15V ± 5%; Slow Memory Mode; T_A = T_{MIN} to T_{MAX} unless otherwise noted, f_{CLK} = 1.25MHz.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
CONVERSION TIME						
MAX172	t_{CONV}	Synchronous (12.5 clock cycles) Asynchronous (12 to 13 clock cycles)	9.6		10 10.4	μs
POWER SUPPLY REJECTION						
V_{DD} Only		FS Change, V_{SS} = -15V, V_{DD} = 4.75V to 5.25V		±1/2		LSB
V_{SS} Only		FS Change, V_{DD} = 5V, V_{SS} = -5% to +5%		±1/8		LSB
POWER REQUIREMENTS						
V_{DD}		±5% for Specified Performance		5		V
V_{SS} (Note 8)		±5% for Specified Performance		-12 or -15		V
I_{DD}		$\overline{CS}$ = $\overline{RD}$ = V_{DD}, AIN = 5V		5	7	mA
I_{SS}		$\overline{CS}$ = $\overline{RD}$ = V_{DD}, AIN = 5V		8	12	mA
Power Dissipation		V_{DD} = +5V, V_{SS} = -15V		145	215	mW

Note 1: Typical change over temp is +1 LSB.
Note 2: V_{DD} = +5V, V_{SS} = -15V, FS = +5.000V, Ideal last code transition = FS - 3/2LSB.
Note 3: Full Scale TC = ΔFS/ΔT, where ΔFS is full scale change from T_A = 25°C to T_{MIN} or T_{MAX}.
Note 4: Includes internal reference drift.
Note 5: V_{REF} TC = $\Delta V_{REF}/\Delta T$, where ΔV_{REF} is reference voltage change from T_A = 25°C to T_{MIN} or T_{MAX}.
Note 6: Output current should not change during conversion.
Note 7: Guaranteed by design, not subject to test.
Note 8: Functional operation at V_{SS} = -12V + 5% is guaranteed by testing offset error and full scale error.

TIMING CHARACTERISTICS (Note 9)

(V_{DD} = +5V, V_{SS} = -12V or -15V; T_A = T_{MIN} to T_{MAX} unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	T_A = 25°C			MAX172C/I		MAX172M		UNITS
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
$\overline{CS}$ to $\overline{RD}$ Setup Time	t_1		0			0		0		ns
$\overline{RD}$ to $\overline{BUSY}$ Delay	t_2	C_L = 50pF		90	190		230		270	ns
Data Access Time (Note 10)	t_3	C_L = 20pF C_L = 100pF		60 70	90 125		110 150		120 170	ns
$\overline{RD}$ Pulse Width	t_4		t_3			t_3		t_3		
$\overline{CS}$ to $\overline{RD}$ Hold Time	t_5		0			0		0		ns
Data Setup Time After $\overline{BUSY}$ Note (10)	t_6				70		90		100	ns
Bus Relinquish Time (Note 11)	t_7		20		75	20	85	20	90	ns
HBEN to $\overline{RD}$ Setup Time	t_8		0			0		0		ns
HBEN to $\overline{RD}$ Hold Time	t_9		0			0		0		ns
Delay Between Read Operations	t_{10}		200			200		200		ns

Note 9: Timing specifications are sample tested at 25°C to ensure compliance. All input control signals are specified with t_r = t_f = 5ns (10% to 90% of +5V) and timed from a voltage level of +1.6V.
Note 10: t_3 and t_6 are measured with the load circuits of Figure 1 and defined as the time required for an output to cross 0.8V or 2.4V.
Note 11: t_7 is defined as the time required for the data lines to change 0.5V when loaded with the circuits of Figure 2.

For additional information on using the MAX172 please refer to MAX162 data sheet.

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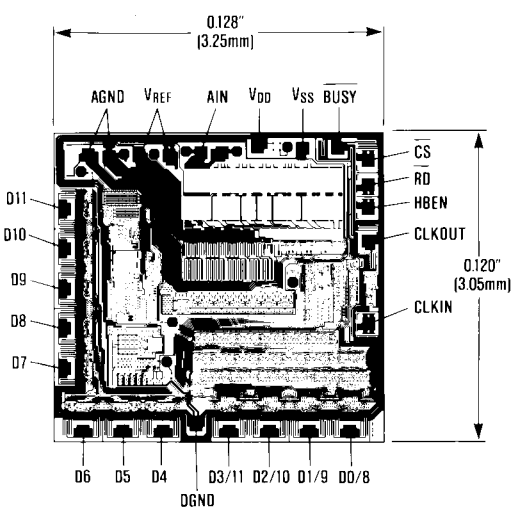
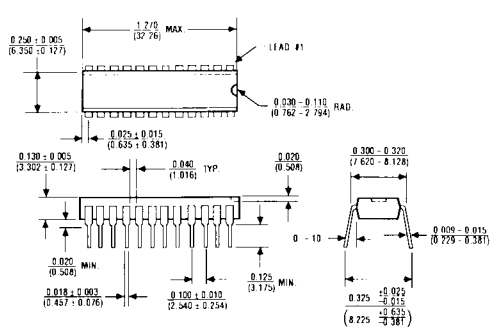
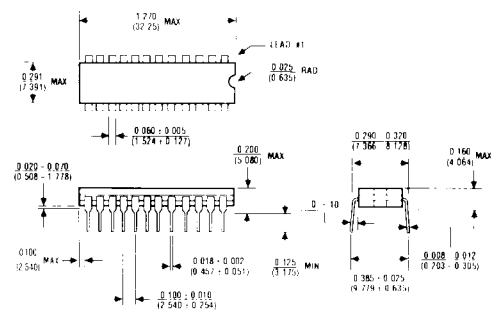
Chip Topography



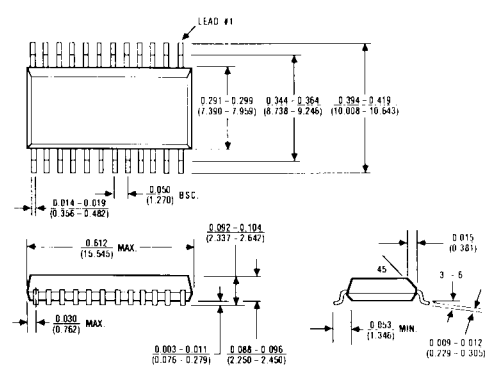
Package Information



24 Lead Plastic Narrow DIP (NG)
θ_{JA} = 120°C/W
θ_{JC} = 60°C/W



24 Lead Narrow CERDIP (RG)
θ_{JA} = 80°C/W
θ_{JC} = 40°C/W



24 Lead Small Outline, Wide (WG)
θ_{JA} = 85°C/W
θ_{JC} = 45° C/W

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